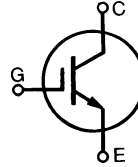


Low $V_{CE(sat)}$ IGBT

Short Circuit SOA Capability

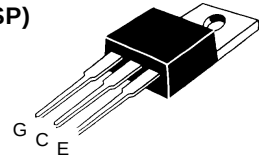
IXSA 16N60
IXSP 16N60

$V_{CES} = 600V$
 $I_{C25} = 16A$
 $V_{CE(sat)typ} = 1.8V$

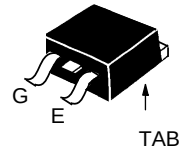


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$; $R_{GE} = 1\text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	32	A
I_{C90}	$T_C = 90^\circ C$	16	A
I_{CM}	$T_C = 25^\circ C$, 1 ms	52	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_J = 125^\circ C$, $R_G = 150\ \Omega$ Clamped inductive load, $L = 300\ \mu H$	$I_{CM} = 32$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15\text{ V}$, $V_{CE} = 360\text{ V}$, $T_J = 125^\circ C$ $R_G = 82\ \Omega$, non repetitive	5	μs
P_C	$T_C = 25^\circ C$	100	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
Weight		2	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ C$
Maximum tab temperature for soldering for 10s		260	$^\circ C$

TO-220AB(IXSP)



TO-263AA



G = Gate,
E = Emitter,

C = Collector,
TAB = Collector

Features

- International standard package
- Guaranteed Short Circuit SOA capability
- Low $V_{CE(sat)}$
 - for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
 - drive simplicity
- Fast fall time for switching speeds up to 20 kHz

Applications

- AC motor speed control
- Uninterruptible power supplies (UPS)
- Welding

Advantages

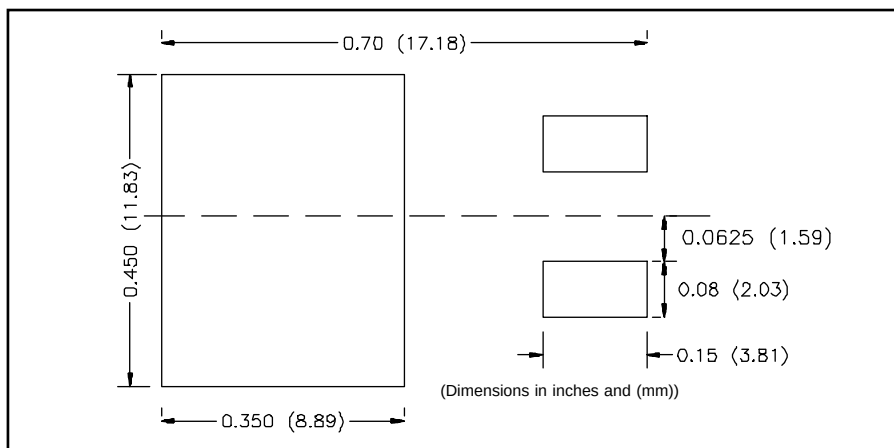
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ C$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250\ \mu A$, $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 750\ \mu A$, $V_{CE} = V_{GE}$	3.5		6.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$			200 μA 1 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$	1.8	2.3	V

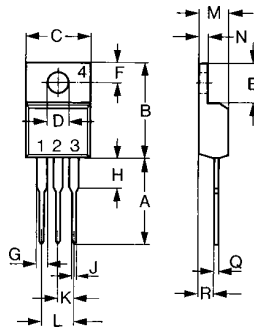
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	3.3	5.0	S
$I_{C(on)}$	$V_{GE} = 15\text{ V}$, $V_{CE} = 10\text{ V}$		50	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		920	pF
C_{oes}			65	pF
C_{res}			14	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		40	nC
Q_{ge}			13	nC
Q_{gc}			18	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 16\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 300\text{ }\mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = 22\text{ }\Omega$		30	ns
t_{ri}			30	ns
$t_{d(off)}$		100	420	ns
t_{fi}		310	470	ns
E_{off}		1.9	2.9	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 16\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 300\text{ }\mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = 22\text{ }\Omega$		30	ns
t_{ri}			30	ns
E_{on}		0.12		mJ
$t_{d(off)}$		150		ns
t_{fi}		510		ns
E_{off}		3.0		mJ
R_{thJC}				1.25 K/W

Note 1: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G

Min. Recommended Footprint

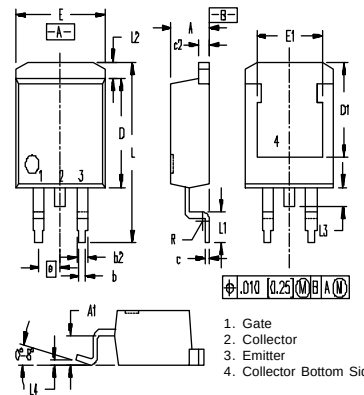


TO-220 AB Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	14.93	0.500	0.580
B	14.23	16.50	0.560	0.650
C	9.66	10.66	0.380	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.29	2.79	0.090	0.110
G	1.15	1.77	0.045	0.070
H	2.79	6.35	0.110	0.250
J	0.64	0.89	0.025	0.035
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	0.64	1.39	0.025	0.055
Q	0.51	0.76	0.020	0.030
R	2.04	2.49	0.080	0.115

TO-263 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025